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MUR190E

MUR1100E

MUR1100E is a

Motorola Preferred Device

SWITCHMODE™ Power Rectifiers

Ultrafast "E" Series with High Reverse Energy Capability

... designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- 20 mjoules Avalanche Energy Guaranteed
- Excellent Protection Against Voltage Transients in Switching Inductive Load Circuits
- Ultrafast 75 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 Volts

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 0.4 gram (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 220°C Max. for 10 Seconds, 1/16" from case
- Shipped in plastic bags, 1000 per bag
- Available Tape and Reeled, 5000 per reel, by adding a "RL" suffix to the part number
- Polarity: Cathode Indicated by Polarity Band
- Marking: U190E, U1100E

MAXIMUM RATINGS

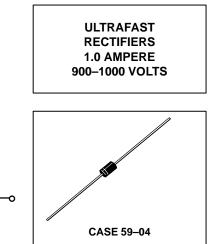
		MUR		
Rating	Symbol	190E	1100E	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	900	1000	Volts
Average Rectified Forward Current (Square Wave) (Mounting Method #3 Per Note 1)	IF(AV)	1.0 @ T _A = 95°C		Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	IFSM	35		Amps
Operating Junction Temperature and Storage Temperature	TJ, Tstg	-65 to +175		°C
THERMAL CHARACTERISTICS				
Maximum Thermal Resistance, Junction to Ambient	R _{θJA}	See Note 1		°C/W

(1) Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

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Preferred devices are Motorola recommended choices for future use and best overall value.

Rev 1





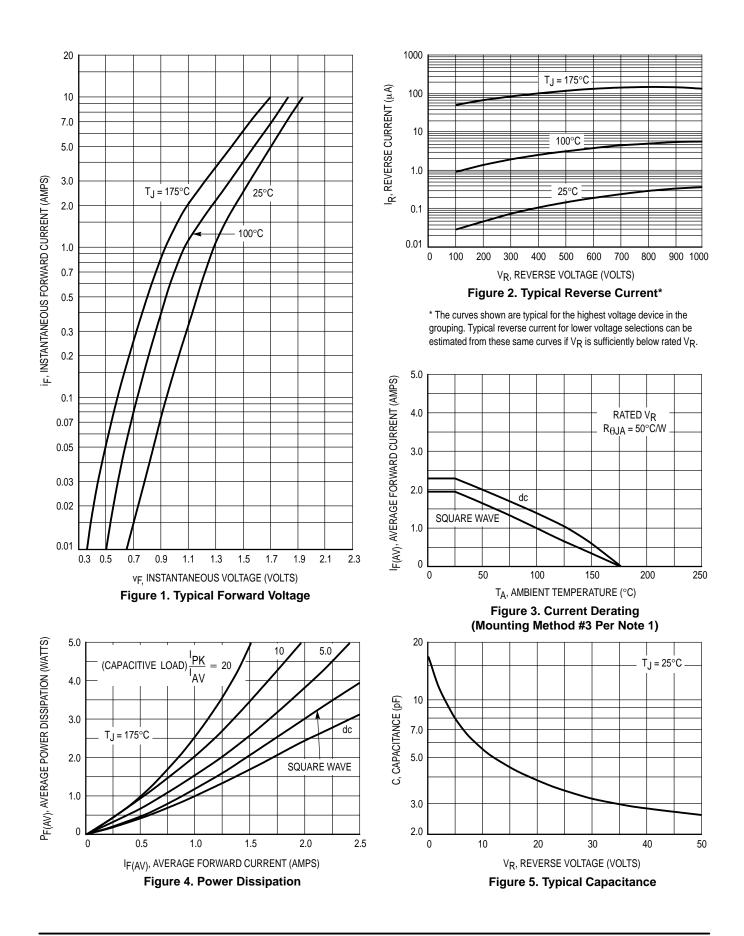
MUR190E MUR1100E

ELECTRICAL CHARACTERISTICS

		MUR		
Rating	Symbol	190E	1100E	Unit
Maximum Instantaneous Forward Voltage (1) ($i_F = 1.0 \text{ Amp}, T_J = 150^{\circ}\text{C}$) ($i_F = 1.0 \text{ Amp}, T_J = 25^{\circ}\text{C}$)	۷F	1.50 1.75		Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, $T_J = 100^{\circ}C$) (Rated dc Voltage, $T_J = 25^{\circ}C$)	ⁱ R	-	00 0	μΑ
Maximum Reverse Recovery Time (I _F = 1.0 Amp, di/dt = 50 Amp/μs) (I _F = 0.5 Amp, i _R = 1.0 Amp, I _{REC} = 0.25 Amp)	trr	-	00 ′5	ns
Maximum Forward Recovery Time (I _F = 1.0 Amp, di/dt = 100 Amp/μs, Recovery to 1.0 V)	tfr	7	75	ns
Controlled Avalanche Energy (See Test Circuit in Figure 6)	WAVAL	1	0	mJ

(1) Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

ELECTRICAL CHARACTERISTICS



MUR190E MUR1100E

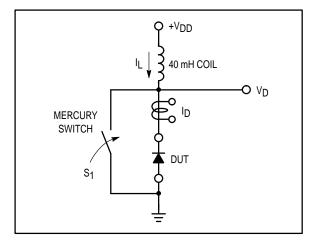


Figure 6. Test Circuit

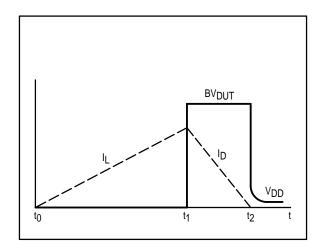


Figure 7. Current–Voltage Waveforms

The unclamped inductive switching circuit shown in Figure 6 was used to demonstrate the controlled avalanche capability of the new "E" series Ultrafast rectifiers. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S₁ is closed at t₀ the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t₁ the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t₂.

By solving the loop equation at the point in time when S₁ is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t₁ to t₂) minus any losses due to finite component resistances. Assuming the component resistive elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S₁ was closed, Equation (2).

The oscilloscope picture in Figure 8, shows the information obtained for the MUR8100E (similar die construction as the MUR1100E Series) in this test circuit conducting a peak current of one ampere at a breakdown voltage of 1300 volts, and using Equation (2) the energy absorbed by the MUR8100E is approximately 20 mjoules.

Although it is not recommended to design for this condition, the new "E" series provides added protection against those unforeseen transient viruses that can produce unexplained random failures in unfriendly environments.

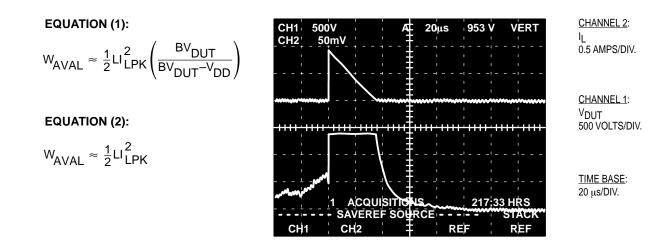


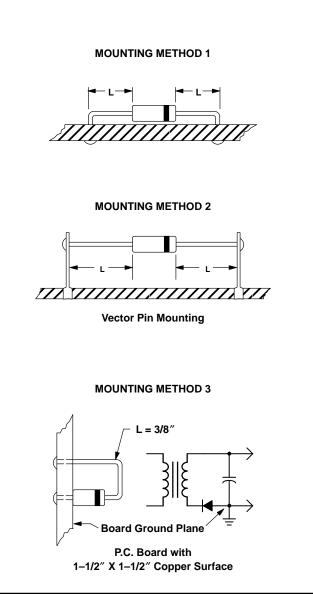
Figure 8. Current–Voltage Waveforms

NOTE 1 — AMBIENT MOUNTING DATA

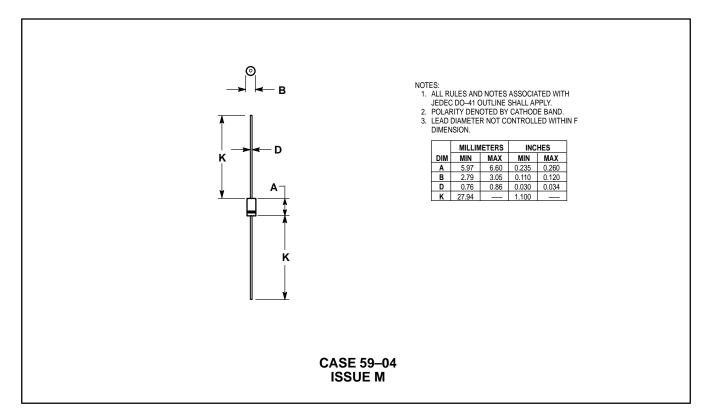
Data shown for thermal resistance junction to ambient ($R_{\theta,JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $\mathsf{R}_{\theta \textbf{J}\textbf{A}}$ IN STILL AIR

Mounti	Mounting		Lead Length, L		
Metho	d	1/8	1/4	1/2	Units
1		52	65	72	°C/W
2	R _{0JA}	67	80	87	°C/W
3			50		°C/W



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